PATENT ABSTRACTS OF JAPAN

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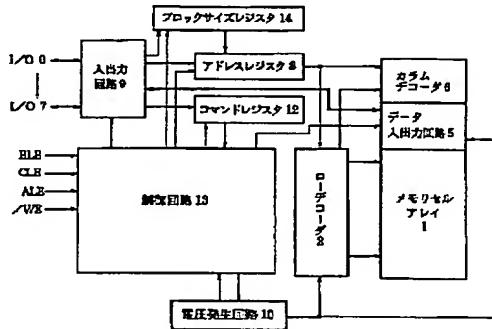|	
(21) Application number: **10053678**	(71) Applicant: **OKI ELECTRIC IND CO LTD**
(22) Date of filing: **05.03.98**	(72) Inventor: **YOSHIDA TAKUJI**

(54) NONVOLATILE SEMICONDUCTOR MEMORY

(57) Abstract:

PROBLEM TO BE SOLVED: To prolong a lifetime of a nonvolatile memory cell by shortening a data rewriting time.

SOLUTION: A memory array 1 has a plurality of nonvolatile memory cells disposed. Data of the cells are erased at a block unit. A block size register 14 stores block size data input externally. The block size data is data for setting one block size (number of nonvolatile memory cells). Accordingly, the block size can be externally set to a desired size. An address register 8 is set in a block size based on the block size data, and generates internal address data for designating the erasure block target from a plurality of the blocks based on the externally input address data. A row decoder 2 and a column decoder 6 select the erasure block target from the internal address data.